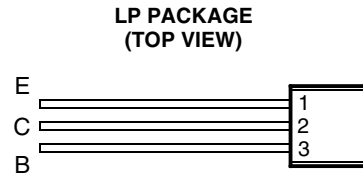


- 20 W Pulsed Power Dissipation
- 100 V Capability
- 2 A Continuous Collector Current
- 4 A Peak Collector Current
- Customer-Specified Selections Available



MDTRAB

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIPP32	V_{CB0}	-40	V
	TIPP32A		-60	
	TIPP32B		-80	
	TIPP32C		-100	
Collector-emitter voltage ($I_B = 0$)	TIPP32	V_{CE0}	-40	V
	TIPP32A		-60	
	TIPP32B		-80	
	TIPP32C		-100	
Emitter-base voltage		V_{EB0}	-5	V
Continuous collector current		I_C	-2	A
Peak collector current (see Note 1)		I_{CM}	-4	A
Continuous base current		I_B	-1	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	0.8	W
Pulsed power dissipation (see Note 3)		P_T	20	W
Operating junction temperature range		T_j	-55 to +150	°C
Storage temperature range		T_{stg}	-55 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 6.4 mW/°C.
 3. $V_{CE} = 20$ V, $I_C = 1$ A, $t_p = 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

MAY 1989 - REVISED SEPTEMBER 2002
 Specifications are subject to change without notice.

TIPP32, TIPP32A, TIPP32B, TIPP32C PNP SILICON POWER TRANSISTORS

BOURNS®

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -5 \text{ mA}$ (see Note 4)	$I_B = 0$	TIPP32 TIPP32A TIPP32B TIPP32C	-40 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -40 \text{ V}$ $V_{CE} = -60 \text{ V}$ $V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIPP32 TIPP32A TIPP32B TIPP32C			-0.2 -0.2 -0.2 -0.2	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIPP32/32A TIPP32B/32C			-0.3 -0.3	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$ $I_C = -2 \text{ A}$	(see Notes 4 and 5)	20 10			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -375 \text{ mA}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-1	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-1.5	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

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